NSN 5961-01-290-8849

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-290-8849
Inclosure Material:
Metal
Overall Length:
0.750 inches
Overall Diameter:
Between 0.501 inches and 0.510 inches
Function For Which Designed:
Bidirectional
Mounting Method:
Press fit
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
400.0 repetitive peak off-state voltage and 20.0 peak gate voltage and -20.0 peak negative gate voltage
Current Rating Per Characteristic:
10.00 amperes forward current, total rms horsepower metric and 100.00 amperes peak forward surge current nanoamperes
Power Rating Per Characteristic:
16.0 watts small-signal input power, common-collector blank and 0.5 watts small-signal input power, common-collector universal
Maximum Operating Tempurature Per Measurement Point:
100.0 degrees celsius junction
Terminal Type And Quantity:
2 tab, solder lug and 1 case
Specification Data:
80131-release 6206 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
No
Fiig:
A110a0